# SHANGHAI SUNRISE ELECTRONICS CO., L1

### RC15S01 THRU RC15S10 SILICON SILASTIC

CELL RECTIFIER

TECHNICAL SPECIFICATION

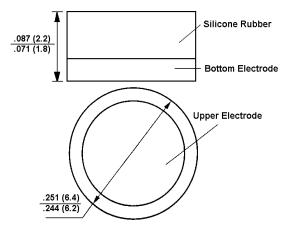
# VOLTAGE: 100 TO 1000V CURRENT: 15A

#### FEATURES

- Low cost
- High surge capability
- Solderable electrode surfaces
- Ideal for hybrids

#### **MECHANICAL DATA**

 Polarity: Bottom or upper electrode denotes cathode according to the notice in package



Dimensions in inches and (millimeters)

## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Single-phase, half-wave, resistive or inductive load rating at 25°C, unless otherwise stated, for capacitive load, d∉ current by 20%)

RATINGS	SYMBOL	RC15S	RC15S	RC15S	RC15S	RC15S	RC15S
		01	02	04	06	08	10
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	100	200	400	600	800	1000
Maximum RMS Voltage	$V_{RMS}$	70	140	280	420	560	700
Maximum DC Blocking Voltage	V <sub>DC</sub>	100	200	400	600	800	1000
Maximum Average Forward Rectified Curren		15					
(T <sub>a</sub> =55°C) (Note 2	) I <sub>F(AV)</sub>						
Peak Forward Surge Current (8.3ms single	1	400					
half sine-wave superimposed on rated load)	I <sub>FSM</sub>						
Maximum Instantaneous Forward Voltage	V <sub>F</sub>	0.95					
(at rated forward current)	۷F						
Maximum DC Reverse Current $T_a=25^{\circ}C$		10					
(at rated DC blocking voltage) $T_a=150^{\circ}C$	, I <sub>R</sub>	500					
Typical Junction Capacitance (Note 1	) C <sub>J</sub>	300					
Typical Thermal Resistance (Note 3	) R <sub>θ</sub> (ja)	1					
Storage and Operation Junction Temperatur	e T <sub>STG</sub> , T <sub>J</sub>	-50 to +150					

Note:

1. Measured at 1 MHz and applied voltage of  $4.0V_{\rm dc}$ 

2. When mounted to heat sink from body.

3. Thermal resistance from junction to ambient.

TD.

TECHNICAL SPECIFICATION

